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AS7C1028

5V 256K X 4 CMOS SRAM (Common I/O)

Features

- Industrial (-40° to 85°C) temperature
- Organization: 262,144 words × 4 bits
- High speed
 - 12 ns address access time
 - 6 ns output enable access time
- Low power consumption via chip deselect
- One chip select plus one Output Enable pin
- Bidirectional data inputs and outputs
- TTL-compatible

- 28-pin JEDEC standard packages - 400 mil SOJ
- ESD protection \geq 2000 volts

Logic block diagram



Pin arrangement

28 Pin SOJ (400 mil)



P. 1 of 8

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Functional description

The AS7C1028 is a 5V high-performance CMOS 1,048,576-bit Static Random-Access Memory (SRAM) device organized as 262,144 words \times 4 bits. It is designed for memory applications requiring fast data access at low voltage, including PentiumTM, PowerPCTM, and portable computing. Alliance's advanced circuit design and process techniques permit 5.0V operation without sacrificing performance or operating margins.

The device enters *standby mode* when \overline{CE} is high. Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 12 ns with output enable access times (t_{OE}) of 6 ns are ideal for high-performance applications. The chip enable (\overline{CE}) input permits easy memory expansion with multiple-bank memory organizations.

A write cycle is accomplished by asserting chip enable ($\overline{\text{CE}}$) and write enable ($\overline{\text{WE}}$) LOW. Data on the input pins I/O0-I/O7 is written on the rising edge of $\overline{\text{WE}}$ (write cycle 1) or $\overline{\text{CE}}$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ($\overline{\text{OE}}$) or write enable ($\overline{\text{WE}}$).

A read cycle is accomplished by asserting chip enable (\overline{CE}) and output enable (\overline{OE}) LOW, with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When chip enable or output enable is high, or write enable is low, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible. Operation is from a single 5.0±0.5V supply. The AS7C1028 is packaged in high volume industry standard packages.

Absolute maximum ratings

| Parameter | Symbol | Min | Max | Unit |
|--|-------------------|------|-----------------------|------|
| Voltage on V _{CC} relative to GND | V _{t1} | -0.5 | +7.0 | V |
| Voltage on any pin relative to GND | V _{t2} | -0.5 | V _{CC} + 0.5 | V |
| Power dissipation | P _D | _ | 1.25 | W |
| Storage temperature (plastic) | T _{stg} | -55 | +125 | °C |
| Ambient temperature with V _{CC} applied | T _{bias} | -55 | +125 | °C |
| DC current into outputs (low) | I _{OUT} | _ | 50 | mA |

Note:

Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

| CE | WE | OE | Data | Mode |
|----|----|----|------------------|---|
| Н | Х | Х | High Z | Standby (I _{SB} , I _{SB1}) |
| L | Н | Н | High Z | Output disable (I _{CC}) |
| L | Н | L | D _{OUT} | Read (I _{CC}) |
| L | L | Х | D _{IN} | Write (I _{CC}) |

Notes:

$$\begin{split} H = V_{IH}, L = V_{IL}, x = \text{Don't care.} \\ V_{LC} = 0.2V, V_{HC} = V_{CC} - 0.2V. \\ \text{Other inputs} \geq V_{HC} \text{ or } V_{LC}. \end{split}$$



Recommended operating conditions

| Parameter | Symbol | Min | Typical | Max | Unit |
|--|-----------------|---------------------|---------|----------------------|------|
| Supply voltage | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| Input voltage | V _{IH} | 2.2 | _ | V _{CC} +0.5 | V |
| out vonage | $V_{IL}^{(1)}$ | -0.5 ⁽¹⁾ | _ | 0.8 | V |
| Ambient operating temperature (Industrial) | T _A | -40 | _ | 85 | °C |

Note:

1 V_{IL} min = -1.5V for pulse width less than 10ns, once per cycle.

DC operating characteristics (over the operating range)^I

| | | | AS7C1 | 028-12 | |
|--------------------------------|------------------|--|-------|--------|------|
| Parameter | Symbol | Test conditions | Min | Max | Unit |
| Input leakage current | ILI | $V_{CC} = Max,$ $V_{in} = GND \text{ to } V_{CC}$ | _ | 5 | μΑ |
| Output leakage current | I _{LO} | $V_{CC} = Max, \overline{CS} = V_{IH},$ $V_{OUT} = GND \text{ to } V_{CC}$ | _ | 5 | μΑ |
| Operating power supply current | I _{CC} | | _ | 170 | mA |
| | I _{SB} | | _ | 40 | mA |
| Standby power supply current | I _{SB1} | $\begin{split} V_{CC} &= Max, \overline{CE} \geq V_{CC} - 0.2V \\ V_{IN} \leq GND + 0.2V \text{ or} \\ V_{IN} \geq V_{CC} - 0.2V, f = 0 \end{split}$ | _ | 10 | mA |
| Output voltage | V _{OL} | $I_{OL} = 8 \text{ mA}, V_{CC} = Min$ | - | 0.4 | V |
| Sulput voltage | V _{OH} | $I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min}$ | 2.4 | - | V |

Capacitance (f = 1MHz, T_a = room temperature, V_{CC} = NOMINAL)²

| Parameter | Symbol | Signals | Test conditions | Max | Unit |
|-------------------|------------------|--|-----------------|-----|------|
| Input capacitance | C _{IN} | A, \overline{CE} , \overline{WE} , \overline{OE} | $V_{in} = 3dV$ | 8 | pF |
| I/O capacitance | C _{I/O} | I/O | $V_{out} = 3dV$ | 8 | pF |

Note:

This parameter is guaranteed by device characterization, but is not production tested.



Read cycle (over the operating range)^{3,9}

| | AS7C1028-12 | | | | |
|---|------------------|-----|-----|------|-------|
| Parameter | Symbol | Min | Max | Unit | Notes |
| Read cycle time | t _{RC} | 12 | _ | ns | |
| Address access time | t _{AA} | _ | 12 | ns | 3 |
| Chip enable (\overline{CE}) access time | t _{ACE} | _ | 12 | ns | 3 |
| Output enable (\overline{OE}) access time | t _{OE} | _ | 6 | ns | |
| Output hold from address change | t _{OH} | 4 | _ | ns | 5 |
| \overline{CE} LOW to output in low Z | t _{CLZ} | 3 | _ | ns | 4, 5 |
| TE HIGH to output in high Z | t _{CHZ} | 0 | 6 | ns | 4, 5 |
| OE LOW to output in low Z | t _{OLZ} | 0 | _ | ns | 4, 5 |
| OE HIGH to output in high Z | t _{OHZ} | 0 | 5 | ns | 4, 5 |
| Power up time | t _{PU} | 0 | - | ns | 4, 5 |
| Power down time | t _{PD} | _ | 12 | ns | 4, 5 |

Key to switching waveforms

Rising input

Undefined output/don't care

Read waveform 1 (address controlled)^{3,6,7,9}



Falling input

Read waveform 2 (CE controlled)^{3,6,8,9}



12/5/06; V.1.0

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Write cycle (over the operating range)¹¹

| | | AS7C1 | 028-12 | | |
|----------------------------------|-----------------|-------|--------|------|-------|
| Parameter | Symbol | Min | Max | Unit | Notes |
| Write cycle time | t _{WC} | 12 | - | ns | |
| Chip enable to write end | t _{CW} | 10 | - | ns | |
| Address setup to write end | t _{AW} | 10 | _ | ns | |
| Address setup time | t _{AS} | 0 | - | ns | |
| Write pulse width | t _{WP} | 10 | _ | ns | |
| Write recovery time | t _{WR} | 0 | _ | ns | |
| Address hold from end of write | t _{AH} | 0 | - | ns | |
| Data valid to write end | t _{DW} | 7 | _ | ns | |
| Data hold time | t _{DH} | 0 | - | ns | 4, 5 |
| Write enable to output in high Z | t _{WZ} | 0 | 5 | ns | 4, 5 |
| Output active from write end | t _{OW} | 3 | - | ns | 4, 5 |

Shaded areas contain advance information.

Write waveform 1 (WE controlled)^{10,11}



Write waveform 2 (CE controlled)^{10,11}



AC test conditions

- Output load: see Figure B or Figure C.
- Input pulse level: GND to V_{CC}. See Figure A.
- Input rise and fall times: 3 ns. See Figure A.
- Input and output timing reference levels: 1.5V.





Notes:

GND

1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.

10%

2 This parameter is sampled, but not 100% tested.

Figure A: Input pulse

- 3 For test conditions, see AC Test Conditions, Figures A, B, C.
- 4 These parameters are specified with CL = 5pF, as in Figures B or C. Transition is measured $\pm 200mV$ from steady-state voltage.
- 5 This parameter is guaranteed, but not tested.
- $\overline{\text{WE}}$ is High for read cycle.

10%

- 7 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are Low for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 CE or WE must be High during address transitions. Either CE or WE asserting high terminates a write cycle.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12 $\overline{\text{CE1}}$ and CE2 have identical timing.
- 13 C=30pF, except on High Z and Low Z parameters, where C=5pF.



Package diagrams



| | 28-pin SOJ | | | | | |
|-----------|----------------|-------|--|--|--|--|
| | 400 mil | | | | | |
| | Min Max | | | | | |
| | in r | nils | | | | |
| Α | 0.132 | .0146 | | | | |
| A1 | 0.062 | - | | | | |
| A2 | 0.105 | 0.115 | | | | |
| B | 0.024 | 0.032 | | | | |
| b | 0.013 | 0.021 | | | | |
| с | 0.720 | 0.012 | | | | |
| D | 0.354 | 0.378 | | | | |
| E | 0.395 | 0.405 | | | | |
| E1 | 0.430 | 0.405 | | | | |
| E2 | 0.430 | 0.440 | | | | |
| e | 0.050 | BSC | | | | |

Note: This part is compatible with both pin numbering conventions used by various manufacturers.

| R R |
|--------|
| ٦ |

Ordering information

| Package | Volt/Temp | 12 ns |
|----------------------|---------------|----------------|
| Plastic SOJ, 400 mil | 5V industrial | AS7C1028-12JIN |

Part numbering system

| AS7C | 1028 | –XX | X | Ι | X |
|-------------|---------------|-------------|---------------------------|--|------------------|
| SRAM prefix | Device number | Access time | Package: J=SOJ 400 mil | Temperature range: $I = -40C$ to $85C$ | N=Lead Free Part |



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